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| FORM PTO-1449 (Modified) | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | ATTY. DOCKET NO. 06150 USA | SERIAL NO. |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) | | APPLICANT Mark Leonard O'Neill, et al. | |
| | | FILING DATE May 23, 2001 | GROUP |

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U.S. PATENT DOCUMENTS

| EXAM- INER INITIAL | DOCUMENT NUMBER | | | | | | | | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPRO- PRIATE |
|--------------------------|-----------------|---|---|---|---|---|---|--|----------|---------------------|-------|----------|------------------------------------|
| Tam | 6 | 1 | 4 | 7 | 0 | 0 | 9 | | 11/14/00 | Grill, et al | 438 | 780 | 6/29/98 |
| | 6 | 1 | 5 | 9 | 8 | 7 | 1 | | 12/12/00 | Loboda, et al | 438 | 786 | 5/29/98 |
| | 6 | 0 | 7 | 7 | 5 | 7 | 4 | | 6/20/00 | Tatsuya Usami | 427 | 579 | 8/18/97 |
| | 6 | 0 | 5 | 4 | 3 | 7 | 9 | | 4/25/00 | Yau, et al | 438 | 623 | 2/11/98 |
| | 5 | 9 | 8 | 9 | 9 | 9 | 8 | | 11/23/99 | Sugahara, et al | 438 | 623 | 8/28/97 |
| | 6 | 0 | 7 | 2 | 2 | 2 | 7 | | 6/6/00 | Yau, et al | 257 | 642 | 7/13/98 |
| | 5 | 8 | 7 | 2 | 0 | 6 | 5 | | 2/16/99 | V. Sivaramakrishnan | 438 | 784 | 4/2/97 |
| | 5 | 8 | 2 | 7 | 7 | 8 | 5 | | 10/27/98 | Bhan, et al | 438 | 784 | 10/24/96 |
| | 5 | 7 | 0 | 3 | 4 | 0 | 4 | | 12/30/97 | M. Matsuura | 257 | 758 | 12/24/96 |
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| | 5 | 5 | 7 | 1 | 5 | 7 | 6 | | 11/5/96 | Qian, et al | 427 | 574 | 2/10/95 |
| | 5 | 6 | 6 | 1 | 0 | 9 | 3 | | 8/26/97 | Ravi, et al | 438 | 763 | 9/12/96 |
| Tam | 5 | 8 | 0 | 0 | 8 | 7 | 7 | | 9/1/98 | Maeda, et al | 427 | 535 | 8/9/96 |

FOREIGN PATENT DOCUMENTS

| | DOCUMENT NUMBER | | | | | | | | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION | |
|-----|-----------------|---|---|---|---|---|---|--|---------|---------|-------|----------|-------------|----|
| | | | | | | | | | | | | | YES | NO |
| Tam | 9 | 9 | 4 | 1 | 4 | 2 | 3 | | 8/19/99 | WO | C23C | | X | |
| | 8 | 1 | 5 | 0 | 0 | 3 | 6 | | 6/2/98 | JP | H01L | 21/31 6 | X | |
| | 9 | 6 | 3 | 2 | 1 | 4 | 9 | | 12/3/96 | JP | H01L | 21/31 4 | X | |
| | 9 | 9 | 1 | 1 | 1 | 7 | 1 | | 4/23/99 | JP | H01L | 21/316 | X | |
| Tam | 9 | 9 | 1 | 1 | 1 | 7 | 1 | | 4/23/99 | JP | H01L | 21/316 | X | |

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| EXAMINER | DATE CONSIDERED 12/10/02 |
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